IRHNMC9A7120

An Infineon Technologies Company

RADIATION HARDENED POWER MOSFET SURFACE MOUNT (SMD-0.2 CERAMIC LID)

100V, N-CHANNEL
R9 TECHNOLOGY

SMD-0.2
(CERAMIC LID)

Product Summary

Part Number	Radiation Level	$R_{DS(on)}$	I_D
IRHNMC9A7120	100 kRads (Si)	55mΩ	23A
IRHNMC9A3120	300 kRads (Si)	55mΩ	23A

Description

IR HiRel R9 technology provides superior power MOSFETs for space applications. These devices have improved immunity to Single Event Effect (SEE) and have been characterized for useful performance with Linear Energy Transfer (LET) up to 90MeV/(mg/cm^2). Their combination of low R_{DS}(on) and faster switching times reduces the power losses and increases power density in today's high speed switching applications such as DC-DC converters and motor controllers. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, and temperature stability of electrical parameters.

Features

- Low R_{DS}(on)
- Fast Switching
- Single Event Effect (SEE) Hardened
- Low Total Gate Charge
- Simple Drive Requirements
- Hermetically Sealed
- Ceramic Package
- Light Weight
- Surface Mount
- ESD Rating: Class 1C per MIL-STD-750, Method 1020

Absolute Maximum Ratings

Pre-Irradiation

Symbol	Parameter	Value	Units
I_{D1} @ V_{GS} = 12V, T_C = 25°C	Continuous Drain Current	23	A
I_{D2} @ V_{GS} = 12V, T_C = 100°C	Continuous Drain Current	14	
I_{DM} @T_C = 25°C	Pulsed Drain Current ①	92	
P_D @T_C = 25°C	Maximum Power Dissipation	54	W
	Linear Derating Factor	0.43	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	392	mJ
I_{AR}	Avalanche Current ①	23	A
E_{AR}	Repetitive Avalanche Energy ①	5.4	mJ
dv/dt	Peak Diode Recovery dv/dt ③	14.6	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Lead Temperature	300 (for 5s)	
	Weight	0.25 (Typical)	g

For Footnotes, refer to the page 2.

Electrical Characteristics @ Tj = 25°C (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	100	—	—	V	V_{GS} = 0V, I_D = 1.0mA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.1	—	V/°C	Reference to 25°C, I_D = 1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	55	mΩ	V_{GS} = 12V, I_{D2} = 14A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 650µA
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-7.7	—	mV/°C	
Gfs	Forward Transconductance	8.0	—	—	S	V_{DS} = 15V, I_{D2} = 14A ④
I_{DSS}	Zero Gate Voltage Drain Current	—	—	1.0	µA	V_{DS} = 80V, V_{GS} = 0V
		—	—	10		V_{DS} = 80V,V_{GS} = 0V,T_J =125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Leakage Reverse	—	—	-100		V_{GS} = -20V
Q_G	Total Gate Charge	—	—	23	nC	I_{D1} = 23A
Q_{GS}	Gate-to-Source Charge	—	—	9.0		V_{DS} = 50V
Q_{GD}	Gate-to-Drain ('Miller') Charge	—	—	9.0		V_{GS} = 12V
$t_{d(on)}$	Turn-On Delay Time	—	—	10	ns	V_{DD} = 50V
tr	Rise Time	—	—	14		I_{D1} = 23A
$t_{d(off)}$	Turn-Off Delay Time	—	—	29		R_G = 7.5Ω
t_f	Fall Time	—	—	7.5		V_{GS} = 12V
Ls +L_D	Total Inductance	—	6.8	—	nH	Measured from center of Drain pad to center of Source pad
C_{iss}	Input Capacitance	—	1180	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	310	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	1.2	—		f = 1.0MHz
R_G	Gate Resistance	—	1.5	—	Ω	f = 1.0MHz, open drain

Source-Drain Diode Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	23	A	
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	92		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	T_J = 25°C,I_S = 23A, V_{GS} = 0V④
t_{rr}	Reverse Recovery Time	—	—	165	ns	T_J = 25°C, I_F = 23A, V_{DD} ≤ 25V
Q_{rr}	Reverse Recovery Charge	—	—	945	nC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	2.3	°C/W

Footnotes:

① Repetitive Rating; Pulse width limited by maximum junction temperature.
② V_{DD} = 25V, starting T_J = 25°C, L = 4.0mH, Peak I_L = 14A, V_{GS} = 20V
③ I_{SD} ≤ 23A, di/dt ≤ 1800A/µs, V_{DD} ≤ 100V, T_J ≤ 150°C
④ Pulse width ≤ 300 µs; Duty Cycle ≤ 2%
⑤ Total Dose Irradiation with V_{GS} Bias. 12 volt V_{GS} applied and V_{DS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.
⑥ Total Dose Irradiation with V_{DS} Bias. 80 volt V_{DS} applied and V_{GS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

Radiation Characteristics

IR HiRel Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR HiRel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

Symbol	Parameter	Up to 300 kRads (Si) [1]		Units	Test Conditions
		Min.	Max.		
BV_{DSS}	Drain-to-Source Breakdown Voltage	100	——	V	V_{GS} = 0V, I_D = 1.0mA
$V_{GS(th)}$	Gate Threshold Voltage	2.0	4.0	V	V_{DS} = V_{GS}, I_D = 650µA
I_{GSS}	Gate-to-Source Leakage Forward	——	100	nA	V_{GS} = 20V
I_{GSS}	Gate-to-Source Leakage Reverse	——	-100	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	——	1.0	µA	V_{DS} = 80V, V_{GS} = 0V
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (TO-3)	——	60	mΩ	V_{GS} = 12V, I_{D2} = 14A
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (SMD-0.2)	——	55	mΩ	V_{GS} = 12V, I_{D2} = 14A
V_{SD}	Diode Forward Voltage	——	1.2	V	V_{GS} = 0V, I_S = 23A

1. Part numbers IRHNMC9A7120 and IRHNCM9A3120

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Typical Single Event Effect Safe Operating Area

LET (MeV/(mg/cm^2))	Energy (MeV)	Range (µm)	VDS (V)			
			@ VGS = 0V	@ VGS = -1V	@ VGS = -5V	@ VGS = -10V
37 ± 5%	417 ± 7.5%	50 ± 7.5%	100	100	100	100
59.8 ± 5%	753 ± 7.5%	60 ± 7.5%	100	100	100	100
89.8 ± 5%	1515 ± 7.5%	82 ± 7.5%	100	100	——	——

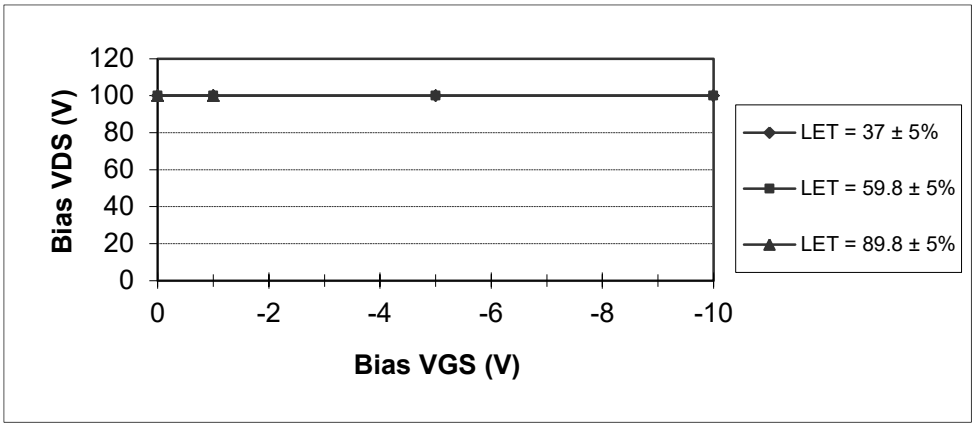


Fig a. Typical Single Event Effect, Safe Operating Area

For Footnotes, refer to the page 2.

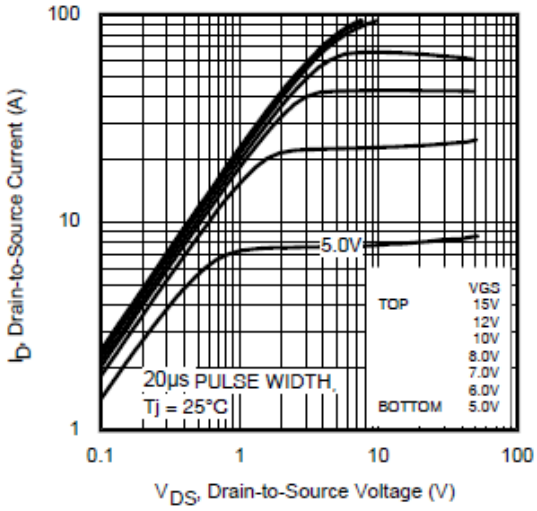


Fig 1. Typical Output Characteristics

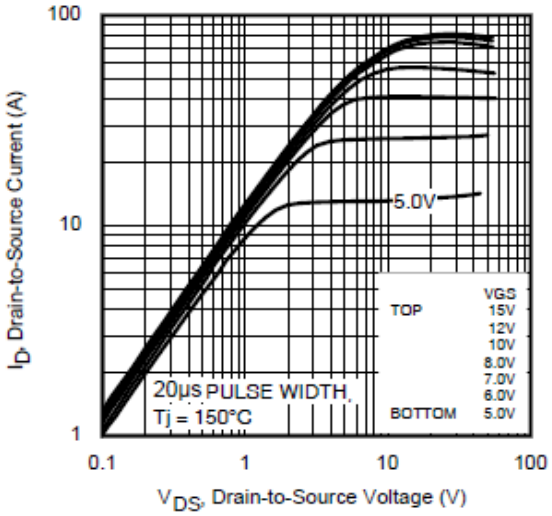


Fig 2. Typical Output Characteristics

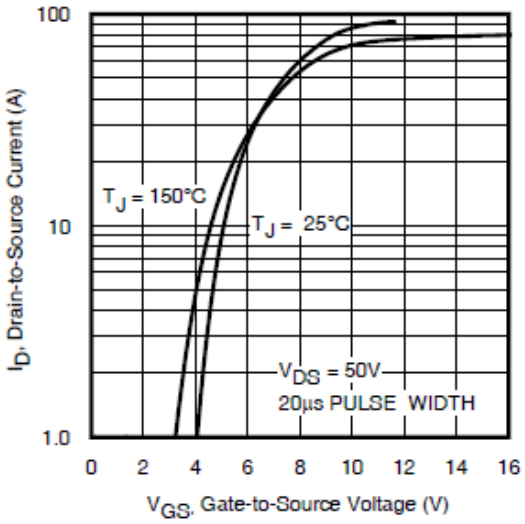


Fig 3. Typical Transfer Characteristics

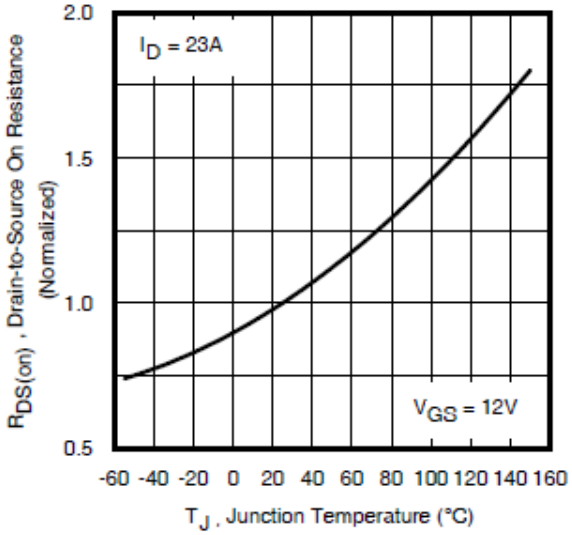


Fig 4. Normalized On-Resistance Vs. Temperature

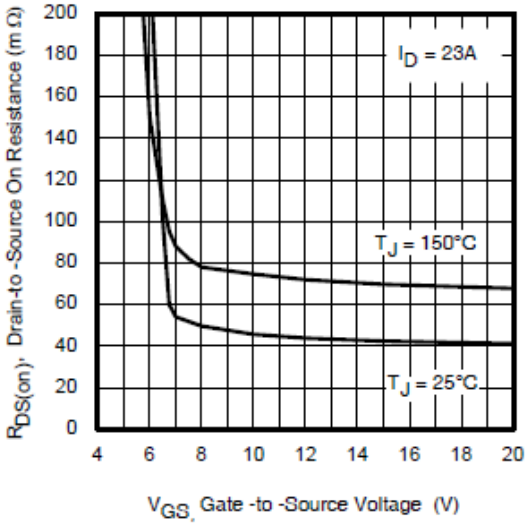


Fig 5. Typical On-Resistance Vs Gate Voltage

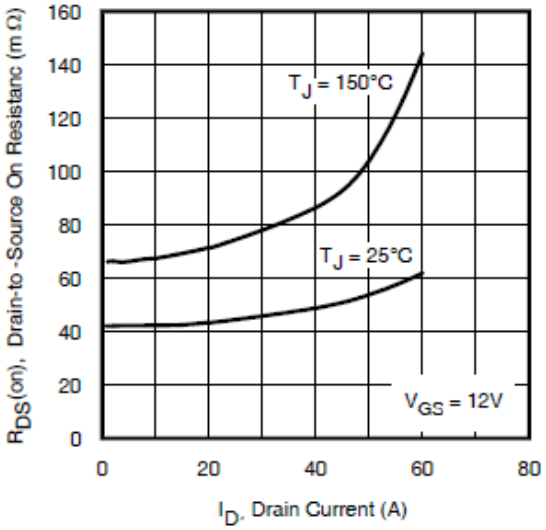


Fig 6. Typical On-Resistance Vs Drain Current

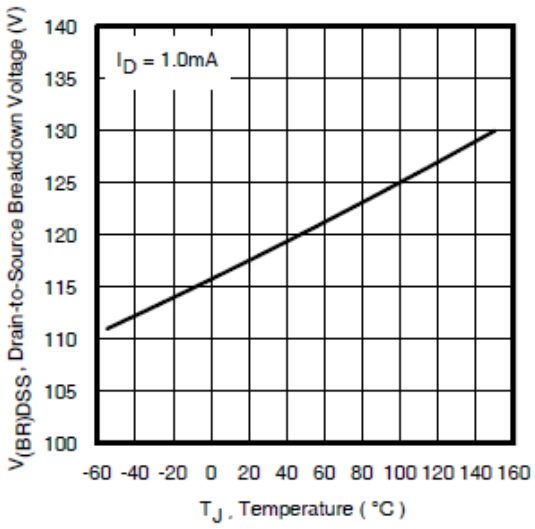


Fig 7. Typical Drain-to-Source Breakdown Voltage Vs Temperature

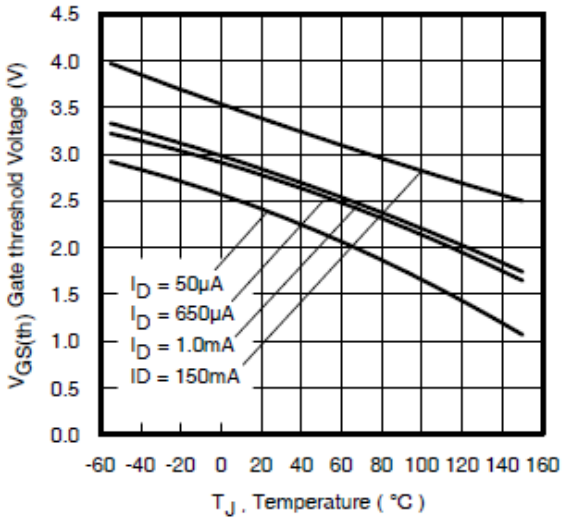


Fig 8. Typical Threshold Voltage Vs Temperature

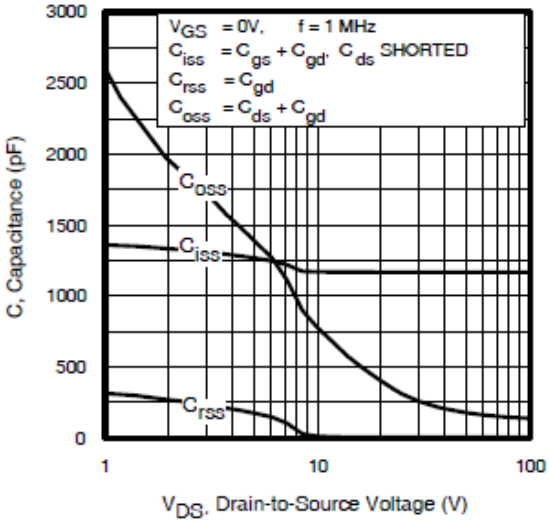


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

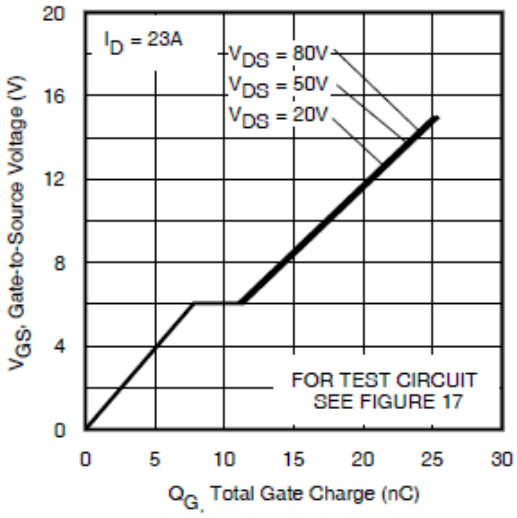


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

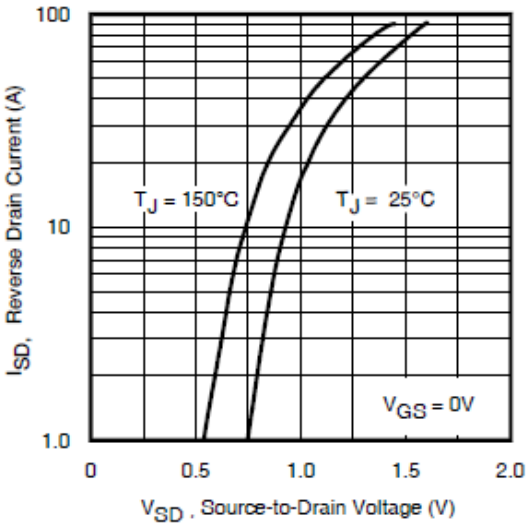


Fig 11. Typical Source-Drain Diode Forward Voltage

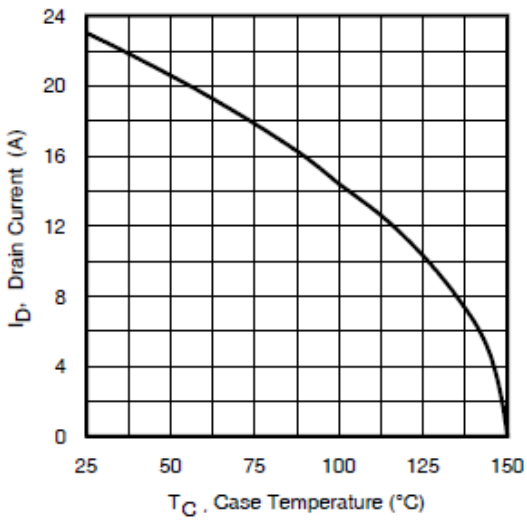


Fig 12. Maximum Drain Current Vs. Case Temperature

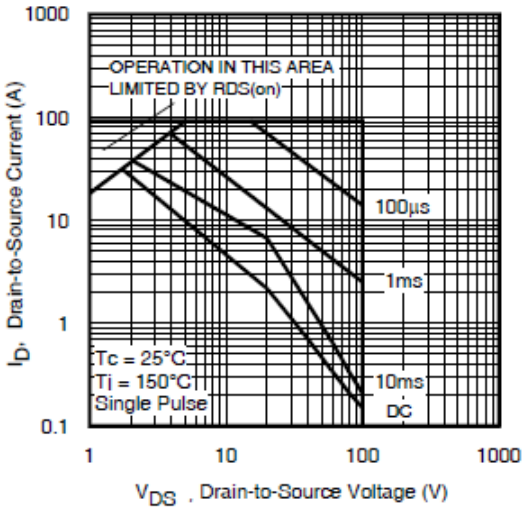


Fig 13. Maximum Safe Operating Area

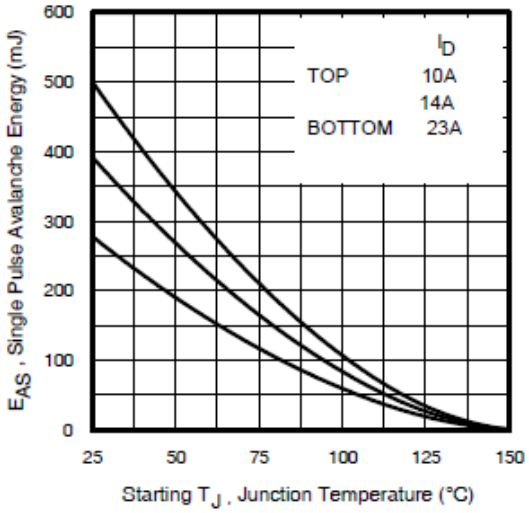


Fig 14. Maximum Avalanche Energy Vs. Drain Current

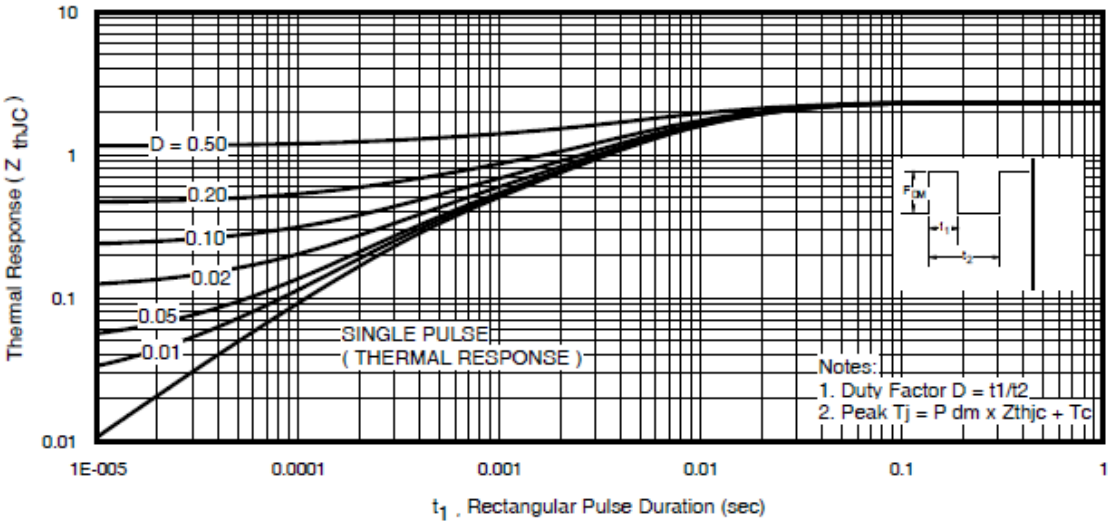


Fig 15. Maximum Effective Transient Thermal Impedance, Junction-to-Case

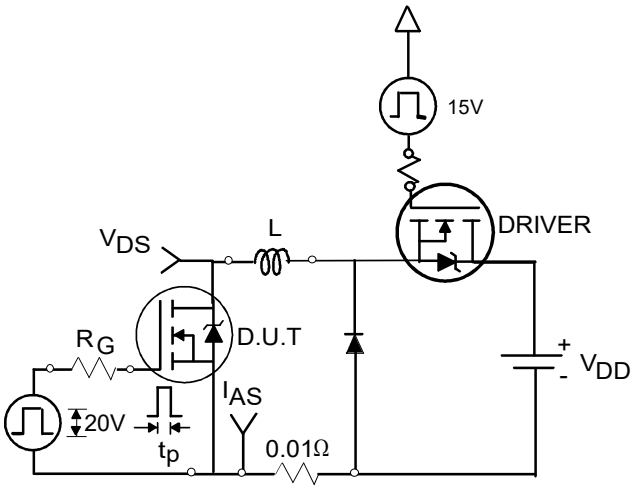


Fig 16a. Unclamped Inductive Test Circuit

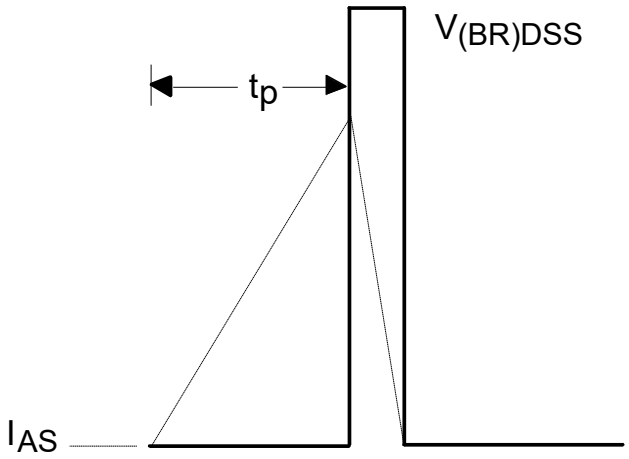


Fig 16b. Unclamped Inductive Wave-

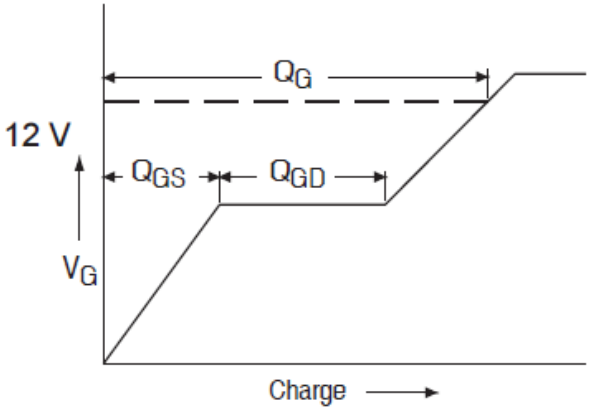


Fig 17a. Gate Charge Waveform

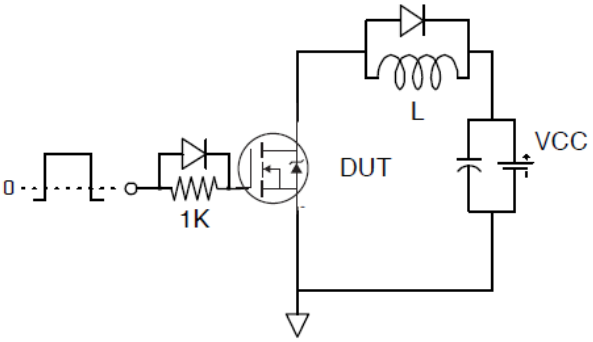


Fig 17b. Gate Charge Test Circuit

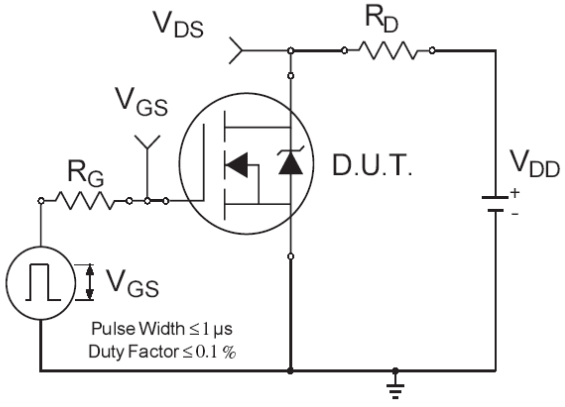


Fig 18a. Switching Time Test Circuit

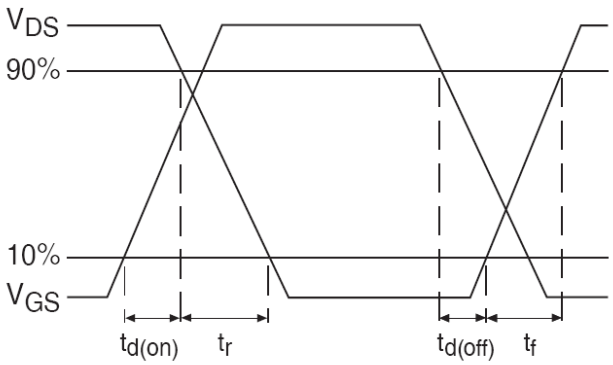
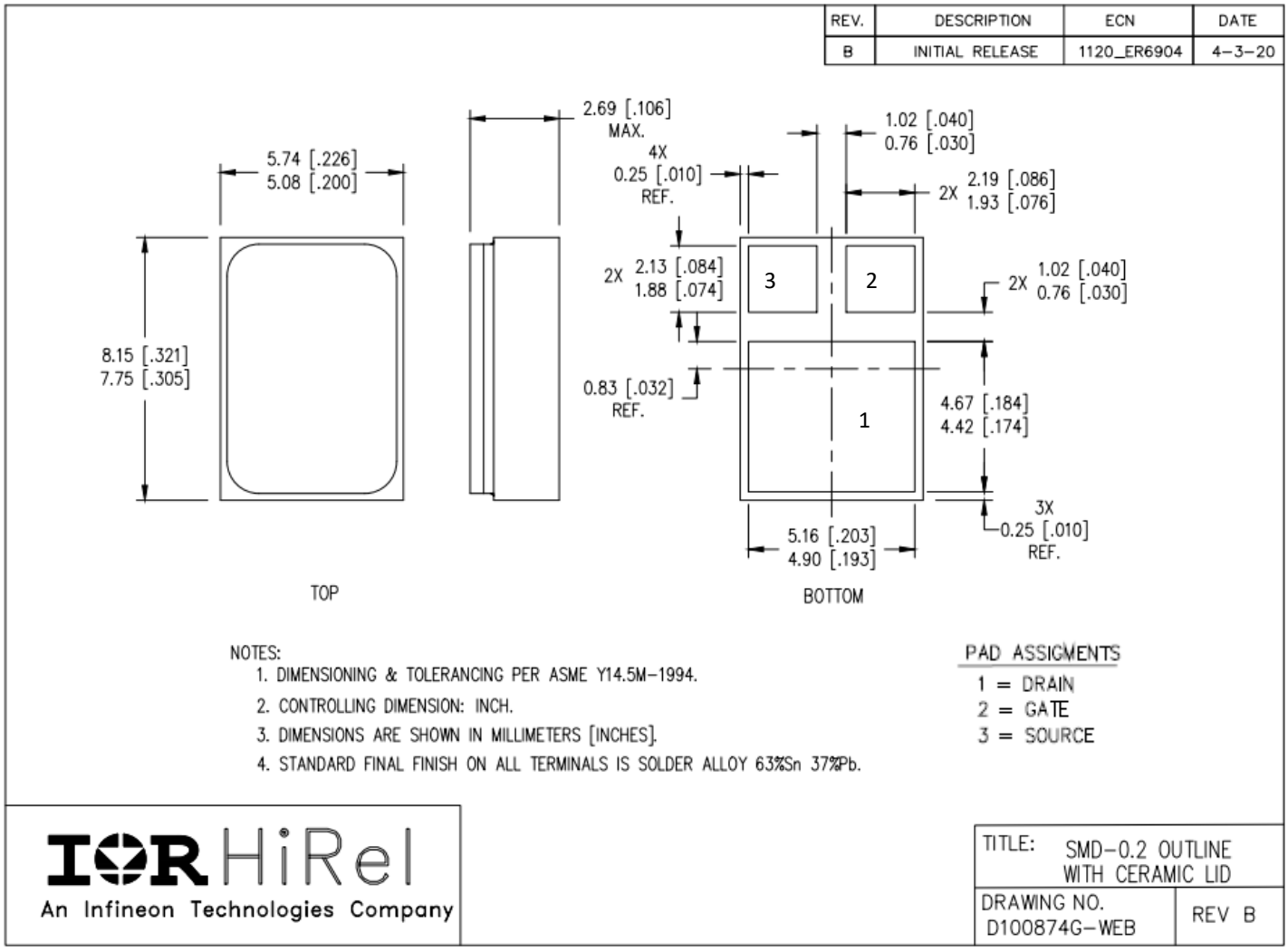


Fig 18b. Switching Time Waveforms

Note: For the most updated package outline, please see the website: SMD-0.2 (Ceramic Lid)

Case Outline and Dimensions — SMD-0.2 (Ceramic Lid)



IMPORTANT NOTICE

The information given in this document shall be in no event regarded as guarantee of conditions or characteristic. The data contained herein is a characterization of the component based on internal standards and is intended to demonstrate and provide guidance for typical part performance. It will require further evaluation, qualification and analysis to determine suitability in the application environment to confirm compliance to your system requirements.

With respect to any example hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind including without limitation warranties on non- infringement of intellectual property rights and any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's product and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of any customer's technical departments to evaluate the suitability of the product for the intended applications and the completeness of the product information given in this document with respect to applications.

For further information on the product, technology, delivery terms and conditions and prices, please contact your local sales representative or go to (www.infineon.com/irhirel).

WARNING

Due to technical requirements products may contain dangerous substances. For information on the types in question, please contact your nearest Infineon Technologies office.